ABSTRACT

A method of manufacturing an electronic device, such as a high-speed semiconductor integrated circuit device, provides improved dimensional accuracy in transferring fine patterns. Photolithography for gate patterns and wiring patterns is carried out by exposing a halftone phase-shift mask having shade areas made of resist with an oblique illumination system, and photolithography for contact hole patterns is carried out by using a photomask having a metal shade film with metal alignment wafer marks.